

## **NPN General Purpose Transistor**

### **NST3904F3T5G**

The NST3904F3T5G device is a spin-off of our popular SOT-23/SOT-323/SOT-563/SOT-963 three-leaded device. It is designed for general purpose amplifier applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

#### **Features**

- h<sub>FE</sub>, 100-300
- Low  $V_{CE(sat)}$ ,  $\leq 0.4 \text{ V}$
- Reduces Board Space
- This is a Pb-Free Device

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	$V_{CEO}$	40	Vdc
Collector - Base Voltage	$V_{CBO}$	60	Vdc
Emitter – Base Voltage	$V_{EBO}$	6.0	Vdc
Collector Current - Continuous	I <sub>C</sub>	200	mAdc

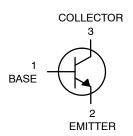
#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 1)	432	°C/W
Total Device Dissipation, T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub> (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub> (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R <sub>ΨJL</sub> (Note 2)	143	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1

- 1. 100 mm<sup>2</sup> 1 oz, copper traces.
   2. 500 mm<sup>2</sup> 1 oz, copper traces.





SOT-1123 **CASE 524AA** STYLE 1

#### **MARKING DIAGRAM**



= Device Code = Date Code

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NST3904F3T5G	SOT-1123 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **NST3904F3T5G**

#### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS			•	•	•
Collector – Emitter Breakdown Voltage (Note 3) (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)		V <sub>(BR)CEO</sub>	40	-	Vdc
Collector - Base Breakdown Voltage	e (I <sub>C</sub> = 10 μAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	60	-	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 10 μAdc, I <sub>C</sub> = 0)		V <sub>(BR)EBO</sub>	6.0	-	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 30 Vdc, V <sub>EB</sub> = 3.0 Vdc)		I <sub>CEX</sub>	-	50	nAdc
ON CHARACTERISTICS (Note 3)				•	
$\label{eq:DC Current Gain} \begin{array}{l} \text{DC Current Gain} \\ \text{($I_{\text{C}}$ = 0.1 mAdc, $V_{\text{CE}}$ = 1.0 Vdc)} \\ \text{($I_{\text{C}}$ = 1.0 mAdc, $V_{\text{CE}}$ = 1.0 Vdc)} \\ \text{($I_{\text{C}}$ = 10 mAdc, $V_{\text{CE}}$ = 1.0 Vdc)} \\ \text{($I_{\text{C}}$ = 50 mAdc, $V_{\text{CE}}$ = 1.0 Vdc)} \\ \text{($I_{\text{C}}$ = 100 mAdc, $V_{\text{CE}}$ = 1.0 Vdc)} \end{array}$		h <sub>FE</sub>	40 70 100 60 30	- 300 - -	-
Collector – Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )		V <sub>CE(sat)</sub>	- -	0.2 0.3	Vdc
Base – Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc) (I <sub>C</sub> = 50 mAdc, I <sub>B</sub> = 5.0 mAdc)		V <sub>BE(sat)</sub>	0.65 -	0.85 1.0	Vdc
SMALL-SIGNAL CHARACTERIS	TICS		•	•	•
Current - Gain - Bandwidth Produc	et (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz)	f <sub>T</sub>	200	_	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	-	4.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz)		C <sub>ibo</sub>	-	8.0	pF
Noise Figure ( $V_{CE}$ = 5.0 Vdc, $I_{C}$ = 100 $\mu$ Adc, $R_{S}$ = 1.0 k $\Omega$ , f = 1.0 kHz)		NF	-	5.0	dB
SWITCHING CHARACTERISTICS					
Delay Time	(V <sub>CC</sub> = 3.0 Vdc, V <sub>BE</sub> = -0.5 Vdc)	t <sub>d</sub>	_	35	
Rise Time (	(I <sub>C</sub> = 10 mAdc, I <sub>B1</sub> = 1.0 mAdc)	t <sub>r</sub>	-	35	ns
Storage Time	(V <sub>CC</sub> = 3.0 Vdc, I <sub>C</sub> = 10 mAdc)	t <sub>s</sub>	-	275	
Fall Time (	(I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mAdc)	t <sub>f</sub>	-	50	- ns

<sup>3.</sup> Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

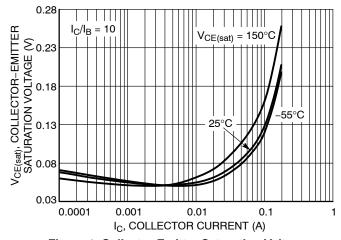


Figure 1. Collector Emitter Saturation Voltage vs.
Collector Current

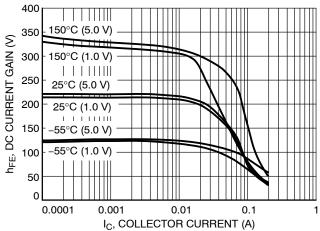


Figure 2. DC Current Gain vs. Collector Current

#### **NST3904F3T5G**

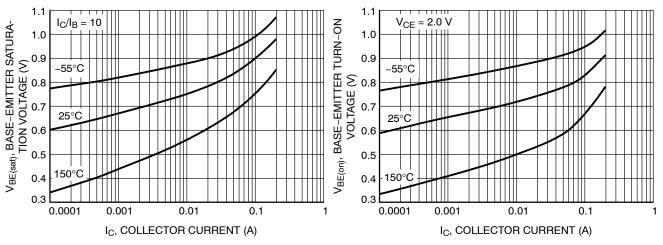


Figure 3. Base Emitter Saturation Voltage vs. Collector Current

Figure 4. Base Emitter Turn-On Voltage vs. Collector Current

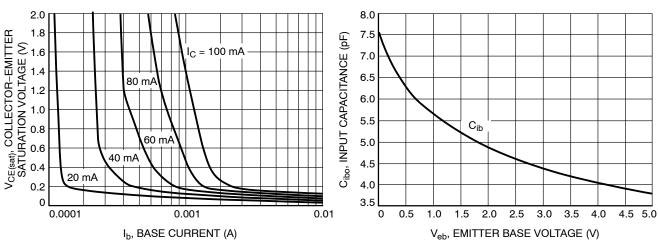


Figure 5. Saturation Region

Figure 6. Input Capacitance

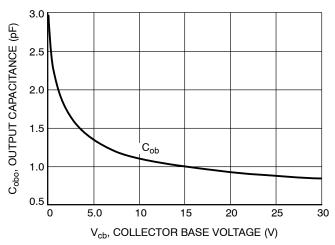


Figure 7. Output Capacitance

# onsemi

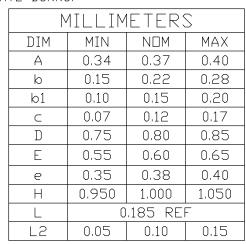


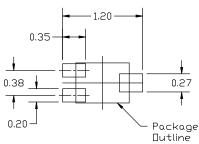
#### SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

**DATE 18 JAN 2024** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- 2. CONTROLLING DIMENSION: MILLIMETERS.
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
  MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS
  OF BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.



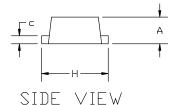


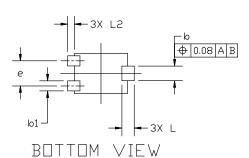
## RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download th e □N Semiconductor Soldering and Mounting Techniques Reference manual, S□L□ERRM/□.

# D A B

TOP VIEW





## GENERIC MARKING DIAGRAM\*



X = Specific Device Code

M = Date Code

Marking.

STYLE 1: STYLE 2

PIN 1. BASE PIN 1.

2 FMITTER

3. COLLECTOR

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE STYLE 5: PIN 1. GATE 2. SOURCE

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DESCRIPTION:	SOT-1123 0.80x0.60x0.37,	0.35P	PAGE 1 OF 1

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<sup>\*</sup>This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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